

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A light-emitting transistor, which is characterized in that it comprises:
 - a) a gate electrode covered with an insulating film;
 - b) a first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;
 - c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 electron-volts; and
 - d) a light-emitter layer provided on the insulating film between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.
2. (Canceled)
3. (Original) The light-emitting transistor according to claim 1, which is characterized in that the second source/drain electrode includes an adhesive base layer made of the electron-injecting material and covered with the hole-injecting material.
4. (Original) The light-emitting transistor according to claim 1, which is characterized in that the first source/drain electrode includes an adhesive base layer made of the hole-injecting material and covered with the electron-injecting material.
5. (Previously Presented) The light-emitting transistor according to claim 1, which is characterized in that the electron-injecting material is aluminum, magnesium, calcium,

magnesium-silver alloy, or a combination of two or more of these materials.

6. (Previously Presented) The light-emitting transistor according to claim 1, which is characterized in that the hole-injecting material is gold, platinum, indium tin oxide, chromium, nickel or a combination of two or more of these materials.

7. (Previously Presented) The light-emitting transistor according to claim 1, which is characterized in that the light-emitter layer includes a light emitter in which a material of an area that is in contact with the first source/drain electrode is different from that of another area that is in contact with the second source/drain electrode, and the area on the side of the first source/drain electrode is made of an electron transport material and the area on the side of the first source/drain electrode is made of a hole transport material.

8. (Previously Presented) The light-emitting transistor according to claim 1, which is characterized in that the thickness of the insulating film satisfies a condition for an interference condition for an emission wavelength of the light emitter layer.

9. (Original) A laser light source, which is characterized in that it comprises:

- a) a gate electrode covered with an insulating film;
- b) a first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;
- c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 electron-volts;
- d) a light-emitter layer provided between the first source/drain electrode and the second

source/drain electrode and made of an organic semiconductor; and

e) a diffraction grating provided between the first source/drain electrode and the second source/drain electrode in order to diffract light emitted from the light-emitter layer.

10. (Original) The laser light source according to claim 9, which is characterized in that the diffraction grating is formed on the gate electrode the first source/drain electrode and the second source/drain electrode.

11. (Currently Amended) A laser light source, which is characterized in that it comprises:

a) a gate electrode covered with an insulating film;

b) a comb-shaped first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;

c) a second source/drain electrode, consisting of a comb-shaped electrode made of a hole-injecting material whose work function is higher than 4.26 electron-volts, which is provided on the insulating film and arranged so that its comb-teeth engage into the comb-teeth of the aforementioned first source/drain electrode to form a diffraction grading consisting of said two sets of comb-teeth; and

d) a light-emitter layer provided between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.

12. (Original) A laser light source, which is characterized in that it comprises:

a) a gate electrode covered with an insulating film;

b) a first source/drain electrode provided on the insulating film and made of an electron-

injecting material whose work function is equal to or lower than 4.26 electron-volts;

c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 electron-volts;

d) a light-emitter layer provided between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor; and

e) a dielectric multi-layer film provided on an optical path from the light-emitter layer to an outside, which causes an interference of light having a predetermined wavelength within an emission band of the light-emitter layer.

13 (New) A light-emitting transistor, which is characterized in that it comprises:

a) a gate electrode covered with an insulating film;

b) a first source/drain electrode provided on the insulating film and made by stacking a layer of an electron-injecting material whose work function is equal to or lower than 4.26 electron volts and a layer of a hole-injecting material whose work function is higher than 4.26 electron-volts;

c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made by stacking a layer of the electron-injecting material and a layer of the hole-injecting material in the same order as the first source/drain electrodes; and

d) a light-emitter layer provided on the insulating film between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.

14 (New) The light-emitting transistor according to claim 13, which is characterized in that the electron-injecting material is aluminum, magnesium, calcium, magnesium-silver alloy, or a combination of two or more of these materials.

15. (New) The light-emitting transistor according to claim 13, which is characterized in that the hole-injecting material is gold, platinum, indium tin oxide, chromium, nickel or a combination of two or more of these materials.

16. (New) The light-emitting transistor according to claim 13, which is characterized in that the light-emitting layer includes a light emitter in which a material of an area that is in contact with the first source/drain electrode is different from that of another area that is in contact with the second source/drain electrode, and the area on the side of the first source/drain electrode is made of an electron transport material and the area on the side of the first source/drain electrode is made of a hole transport material.

17. (New) The light-emitting transistor according to claim 13, which is characterized in that the thickness of the insulating film satisfies a condition for an interference condition for an emission wavelength of the light emitter layer.